Medium power transistor (-30V, -2.0A) 2SA2049

Features

- 1) High speed switching. (Tf: Typ.: 20ns at Ic = -2.0A)
- 2) Low saturation voltage, typically

(Typ.: -250mV at Ic = -1.0A, IB = -100mA)

- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SC5731

Applications

Small signal low frequency amplifier High speed switching

Structure

PNP Silicon epitaxial planar transistor

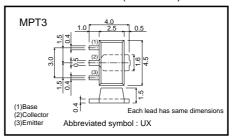
Packaging specifications

	Package	Taping
Туре	Code	T100
	Basic ordering unit (pieces)	1000
2SA2049		0

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-30	V
Collector-emitter voltage	Vceo	-30	V
Emitter-base voltage	Vево	-6	V
Collector current	Ic	-2.0	Α
Collector current	Іср	-4.0	A *1
Dower dissination	D-	500	mW
Power dissipation	Pc	2.0	W *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55~+150	°C

●External dimensions (Units : mm)



^{*1} Pw=100ms
*2 Mounted on a 40×40×0.7 (mm) ceramic substrate

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-30	_	_	V	Ic= -100μA	
Collector-emitter breakdown voltage	BVceo	-30	_	_	V	Ic=-1mA	
Emitter-base breakdown voltage	ВУево	-6	_	_	V	I _E = -100μA	
Collector cut-off current	Ісво	_	_	-1.0	μΑ	V _{CB} = -20V	
Emitter cut-off current	ІЕВО	_	_	-1.0	μΑ	V _{EB} = -4V	
Collector-emitter saturation voltage	VCE (sat)	_	-250	-500	mV	Ic= -1.0A, I _B = -100mA	
DC current gain	hfe	120	_	390	_	VcE= -2V, Ic= -100mA	
Transition frequency	f⊤	_	350	_	MHz	Vc=-10V, I=100mA, f=10MHz	
Collector output capacitance	Cob	_	25	_	pF	Vcb= -10V, Ie=0A, f=1MHz	
Turn-on time	Ton	_	25	_	ns	Ic= -2.0A	
Storage time	Tstg	_	100	_	ns	Iв₁= –200mA Iв₂=200mA Vcc	
Fall time	Tf	_	20	_	ns		

●hFE RANK

Q	R
120–270	180-390

•Electrical characteristic curves

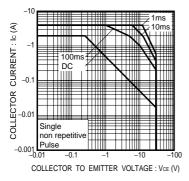


Fig.1 Safe Operating Area

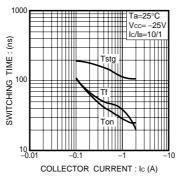


Fig.2 Switching Time

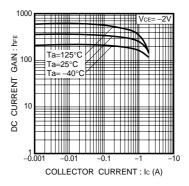


Fig.3 DC Current Gain vs. Collector Current (I)

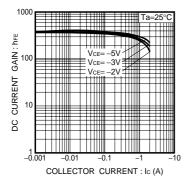


Fig.4 DC Current Gain vs. Collector Current (II)

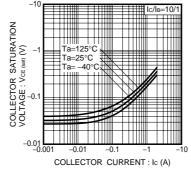


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

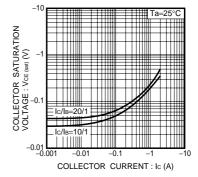


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

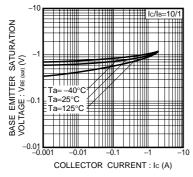


Fig.7 Base-Emitter Saturation Voltage vs.Collecter Current

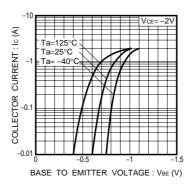


Fig.8 Grounded Emitter Propagation Characteristics

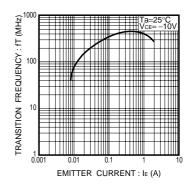


Fig.9 Transition Frequency

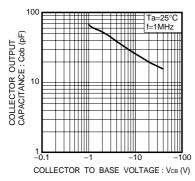
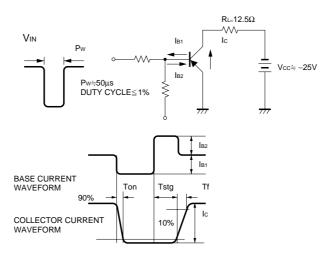


Fig.10 Collector Output Capacitance

•Switching characteristics measurement circuits



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